MMBTSA1980W

PNP Silicon Epitaxial Planar Transistor

for general small signal amplifier applications.

The transistor is subdivided into four groups, O, Y, G and L, according to its DC current gain.



1.Base 2.Emitter 3.Collector SOT-323 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	-V _{CBO}	50	V
Collector-Emitter Voltage	-V _{CEO}	50	V
Emitter-Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	150	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _S	-55 +150	°C

Characteristics at T_{amb} = 25 °C

Parameter		Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 6 \text{ V}$, $-I_C = 2 \text{ mA}$ Current Gain Group	O Y G L	h _{FE} h _{FE} h _{FE}	70 120 200 300	140 240 400 700	- - -
Collector Base Breakdown Voltage at -I _C = 100 µA		-V _{(BR)CBO}	50	-	V
Collector Emitter Breakdown Voltage at -I _C = 1 mA		-V _{(BR)CEO}	50	-	V
Emitter Base Breakdown Voltage at -I _E = 10 μA		-V _{(BR)EBO}	5	-	٧
Collector Cutoff Current at -V _{CB} = 50 V		-I _{CBO}	-	0.1	μΑ
Emitter Cutoff Current at -V _{EB} = 5 V		-I _{EBO}	-	0.1	μΑ
Collector Emitter Saturation Voltage at $-I_C = 100$ mA, $-I_B = 10$ mA		-V _{CE(sat)}	1	0.3	٧
Transition Frequency at $-V_{CE} = 10 \text{ V}$, $-I_C = 1 \text{ mA}$		f _T	80	-	MHz
Collector Output Capacitance at -V _{CB} = 10 V, f = 1 MHz		СОВ	-	7	pF
Noise Figure at -V _{CE} = 6 V, -I _C = 0.1 mA, f = 1 KHz, R _G = 10 K Ω		NF	-	10	dB



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Dated: 30/03/2006

Fig. 1 P_C-T_a

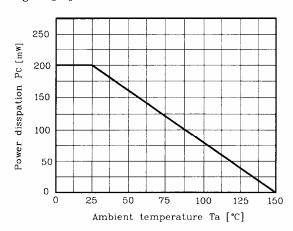


Fig. 3 $I_{\rm C}.V_{\rm CE}$

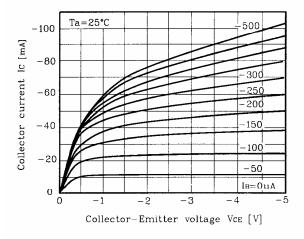


Fig. 5 $V_{\text{CE(sat)-}}I_{\text{C}}$

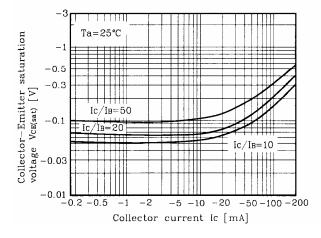


Fig. 2 I_{C} - V_{BE}

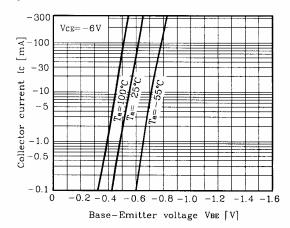
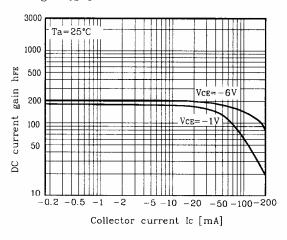


Fig. 4 h_{FE}.I_C





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